



# STP100NF03L-03

## STB100NF03L-03 STB100NF03L-03-1

N-channel 30V - 0.0026Ω - 100A - D<sup>2</sup>PAK/I<sup>2</sup>/TO-220  
STripFET™ III Power MOSFET

### General features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STB100NF03L-03	30V	<0.0032Ω	100A
STB100NF03L-03-1	30V	<0.0032Ω	100A
STP100NF03L-03	30V	<0.0032Ω	100A

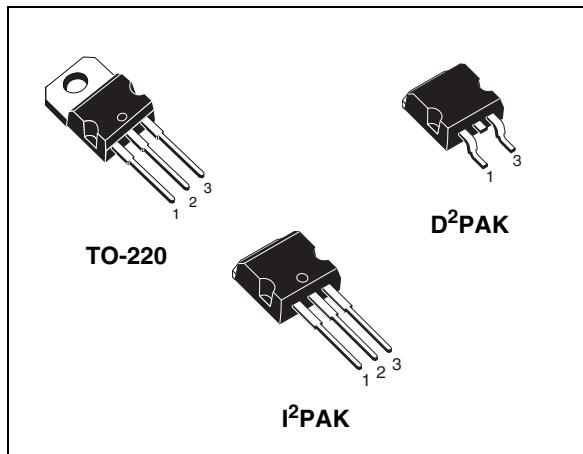
- Low threshold drive
- 100% avalanche tested
- Logic level device

### Description

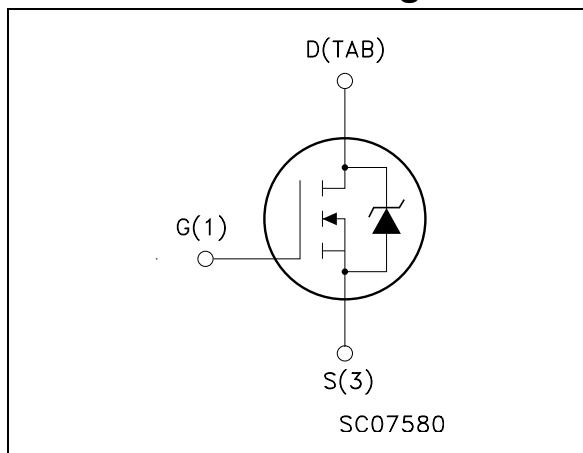
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

### Applications

- Switching application



### Internal schematic diagram



### Order codes

Part number	Marking	Package	Packaging
STB100NF03L-03T4	B100NF03L	D <sup>2</sup> PAK	Tape & reel
STB100NF03L-03-1	B100NF03L	I <sup>2</sup> PAK	Tube
STP100NF03L-03	P100NF03L	TO-220	Tube

## Contents

<b>1</b>	<b>Electrical ratings</b>	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b>	<b>4</b>
2.1	Electrical characteristics (curves)	6
<b>3</b>	<b>Test circuit</b>	<b>8</b>
<b>4</b>	<b>Package mechanical data</b>	<b>9</b>
<b>5</b>	<b>Packaging mechanical data</b>	<b>13</b>
<b>6</b>	<b>Revision history</b>	<b>14</b>

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	30	V
$V_{DGR}$	Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )	24	V
$V_{GS}$	Gate- source voltage	$\pm 16$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	100	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	100	A
$I_{DM}^{(2)}$	Drain current (pulsed)	400	A
$P_{tot}$	Total dissipation at $T_C = 25^\circ\text{C}$	300	W
	Derating Factor	2	W/ $^\circ\text{C}$
$E_{AS}^{(3)}$	Single pulse avalanche energy	1.9	J
$T_{stg}$	Storage temperature	-55 to 175	$^\circ\text{C}$
$T_j$	Max. operating junction temperature		

1. Value limited by wire bonding
2. Pulse width limited by safe operating area.
3. Starting  $T_j = 25^\circ\text{C}$ ,  $I_D = 50\text{A}$ ,  $V_{DD} = 50\text{V}$

**Table 2. Thermal data**

$R_{thj-case}$	Thermal resistance junction-case max	0.5	$^\circ\text{C/W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	$^\circ\text{C/W}$
$T_J$	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

## 2 Electrical characteristics

( $T_{CASE}=25^\circ\text{C}$  unless otherwise specified)

**Table 3. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu\text{A}, V_{GS} = 0$	30			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{max ratings}$ $V_{DS} = \text{max ratings}, T_C = 125^\circ\text{C}$			1 10	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 16\text{V}$			$\pm 100$	nA
$V_{GS(\text{th})}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1	1.7	2.5	V
$R_{DS(\text{on})}$	Static drain-source on resistance	$V_{GS} = 10\text{V}, I_D = 50\text{A}$ $V_{GS} = 4.5\text{V}, I_D = 50\text{A}$		0.0026 0.0032 0.0045	0.0032 0.0045	$\Omega$ $\Omega$

**Table 4. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} > I_{D(\text{on})} \times R_{DS(\text{on})} \text{max}, I_D = 30\text{A}$	10			s
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{V}, f = 1\text{MHz}, V_{GS} = 0$		6200 1720 300		pF pF pF
$t_{d(\text{on})}$ $t_r$ $t_{d(\text{off})}$ $t_f$	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 15\text{V}, I_D = 50\text{A}$ $R_G = 4.7\Omega, V_{GS} = 4.5\text{V}$ (see <a href="#">Figure 13</a> )		35 315 115 95		ns ns ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 24\text{V}, I_D = 100\text{A}, V_{GS} = 5\text{V}$ (see <a href="#">Figure 14</a> )		88 22.5 36		nC nC nC

1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.

**Table 5. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				100 400	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 100A, V_{GS} = 0$			1.3	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 100A,$ $d/dt = 100A/\mu s,$ $V_{DD} = 20V, T_j = 150^\circ C$ (see <i>Figure 15</i> )		75 150 4		ns nC A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

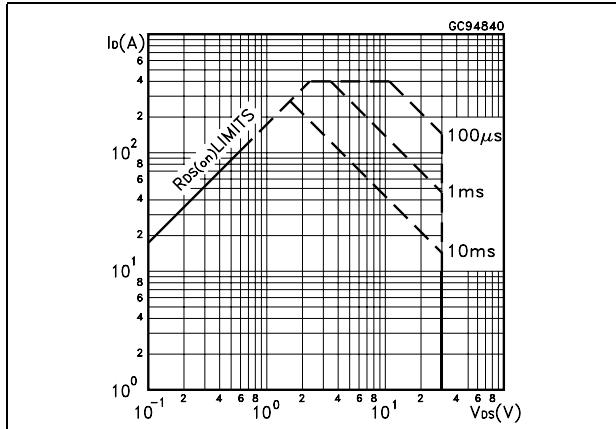


Figure 2. Thermal impedance

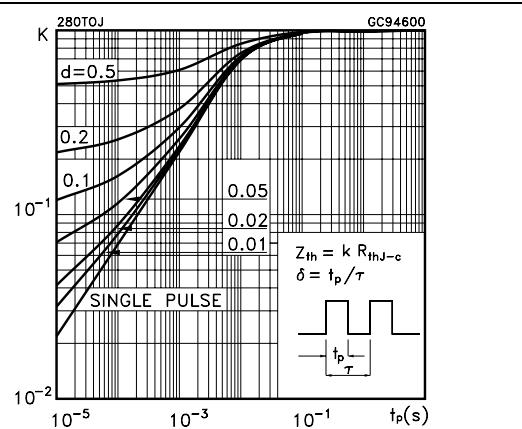


Figure 3. Output characteristics

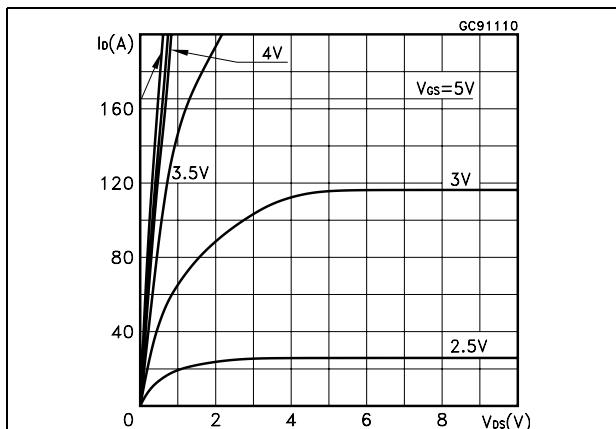


Figure 4. Transfer characteristics

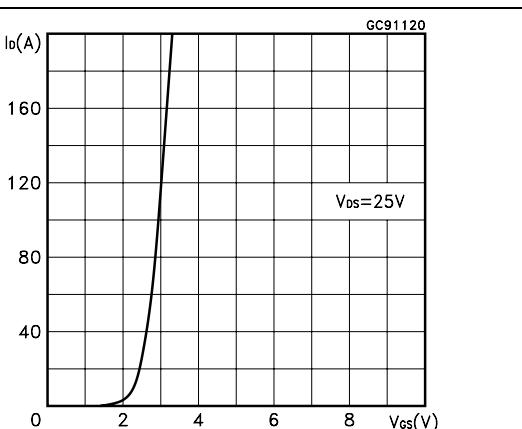


Figure 5. Transconductance

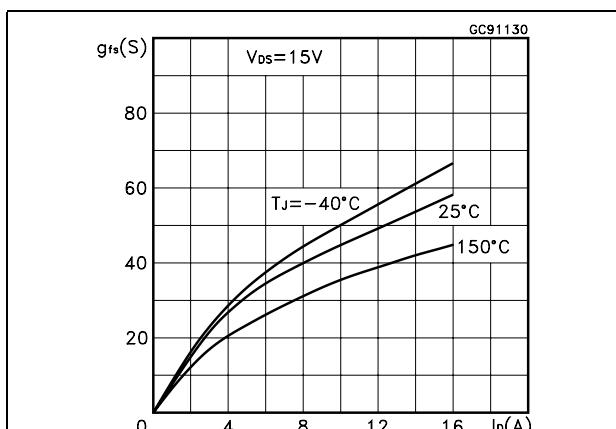
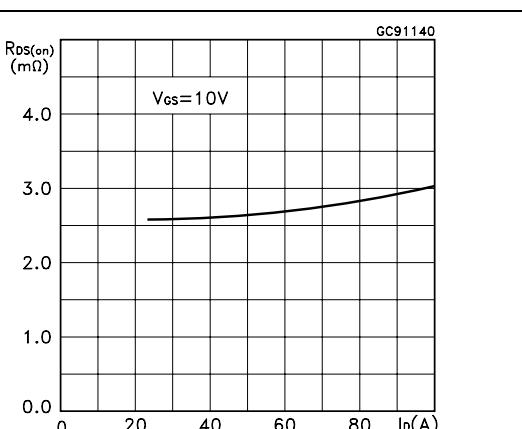
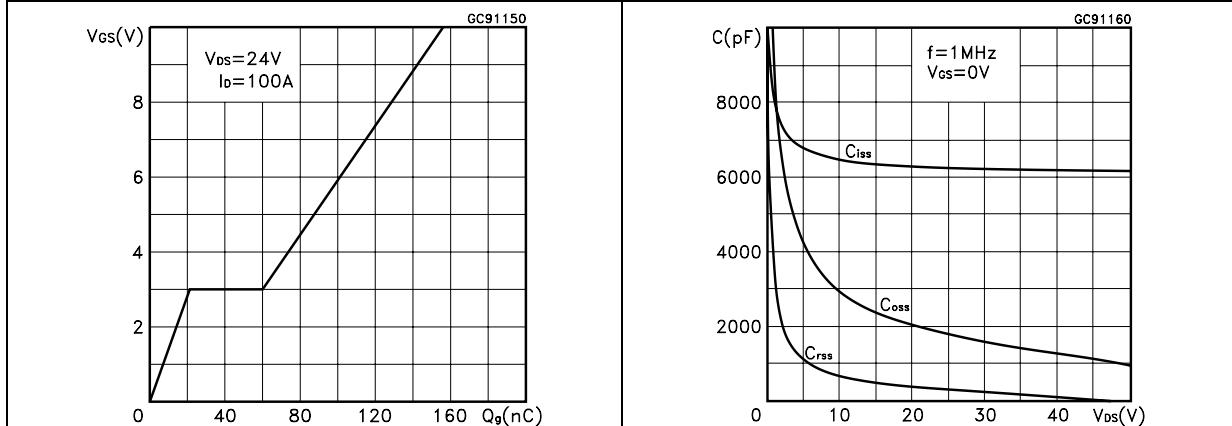
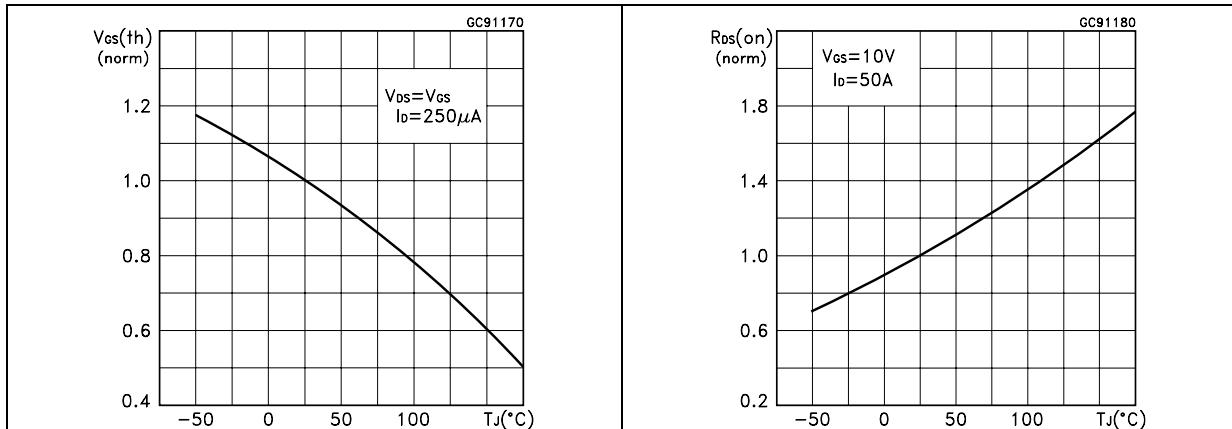
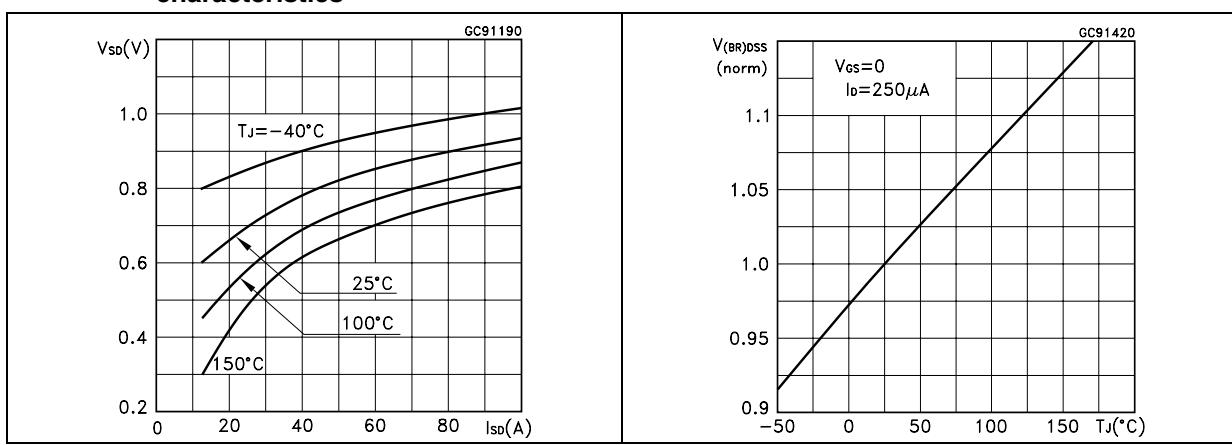


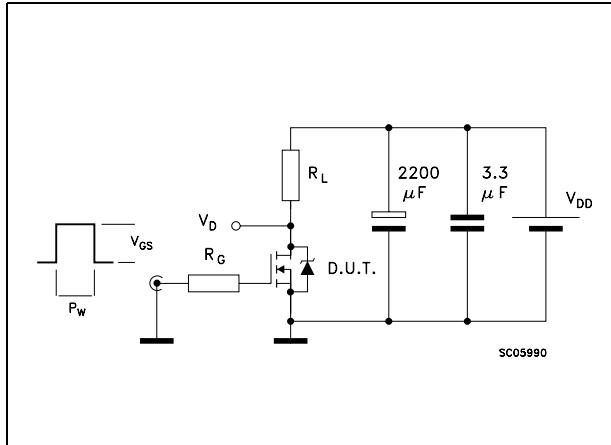
Figure 6. Static drain-source on resistance



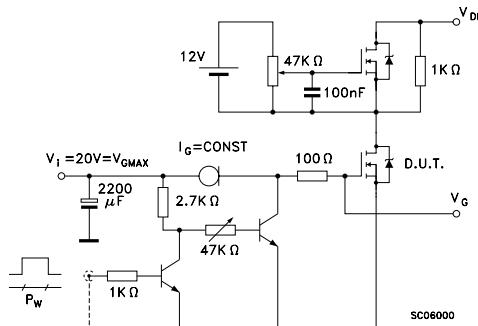
**Figure 7.** Gate charge vs gate-source voltage    **Figure 8.** Capacitance variations**Figure 9.** Normalized gate threshold voltage vs temperature**Figure 10.** Normalized on resistance vs temperature**Figure 11.** Source-drain diode forward characteristics**Figure 12.** Normalized  $B_{VDSS}$  vs temperature

### 3 Test circuit

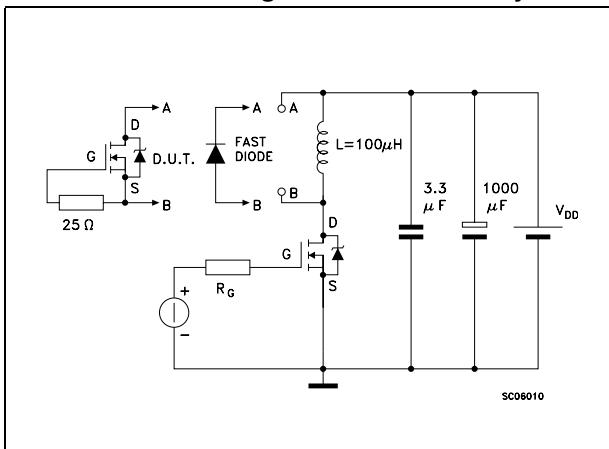
**Figure 13.** Switching times test circuit for resistive load



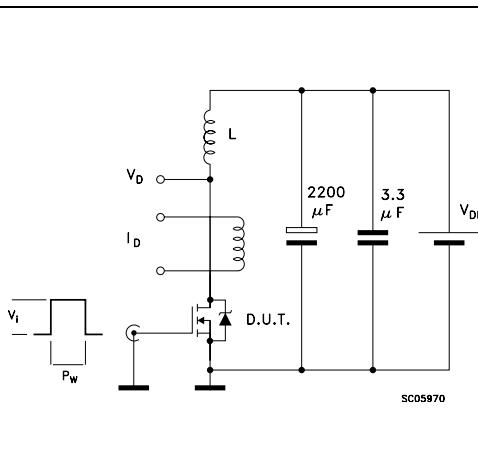
**Figure 14.** Gate charge test circuit



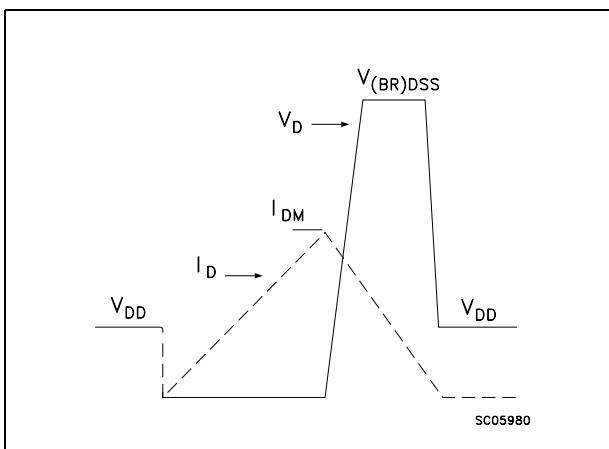
**Figure 15.** Test circuit for inductive load switching and diode recovery times



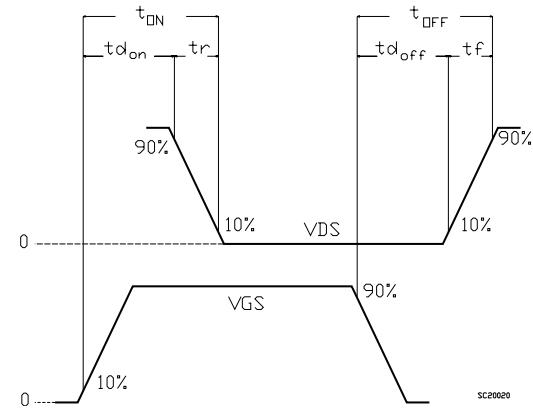
**Figure 16.** Unclamped Inductive load test circuit



**Figure 17.** Unclamped inductive waveform



**Figure 18.** Switching time waveform

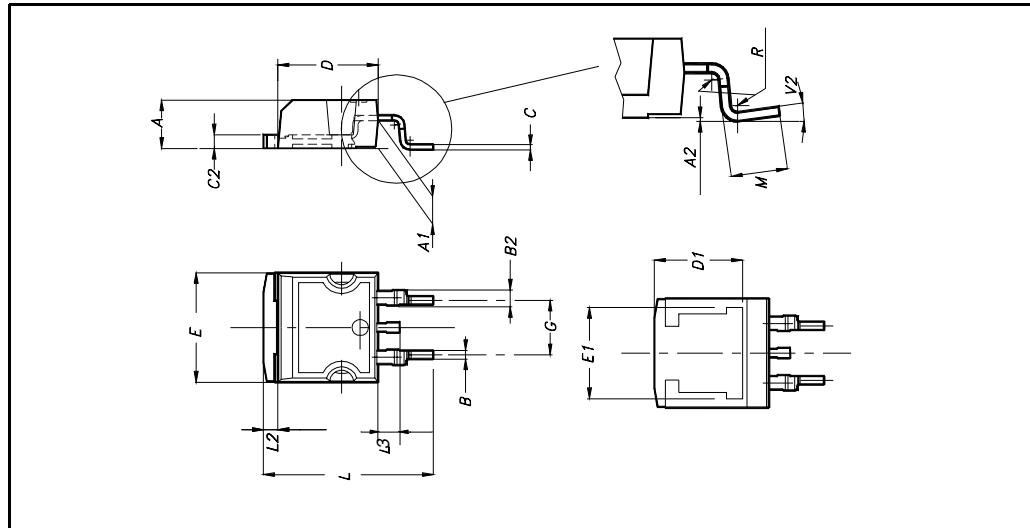


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

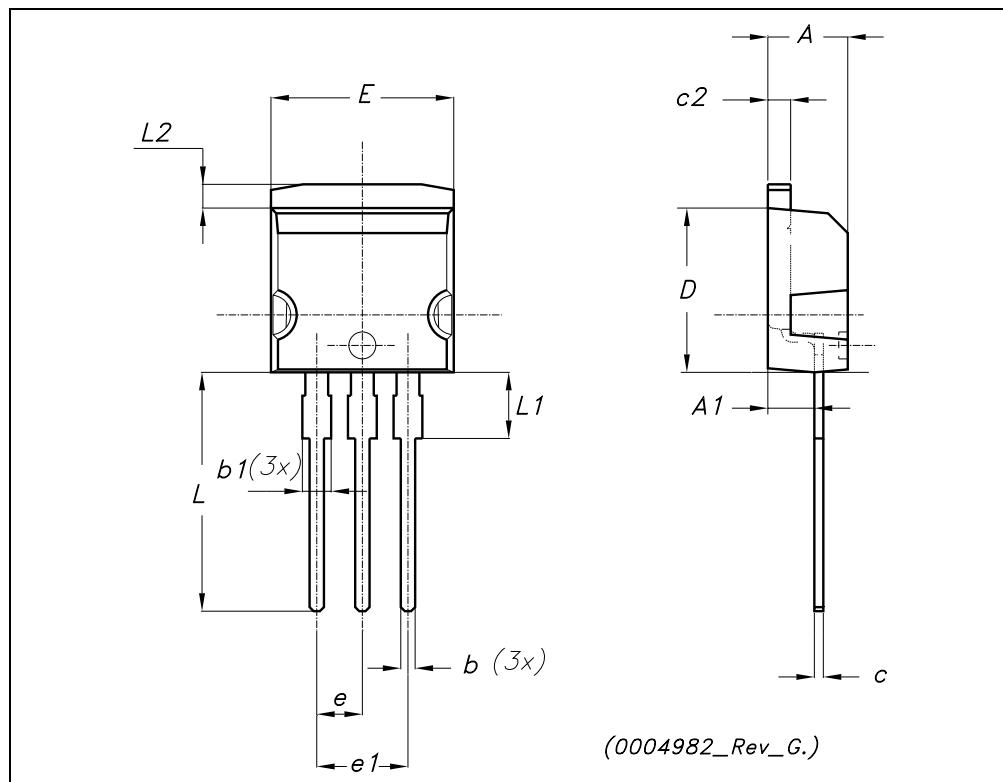
**D<sup>2</sup>PAK MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			



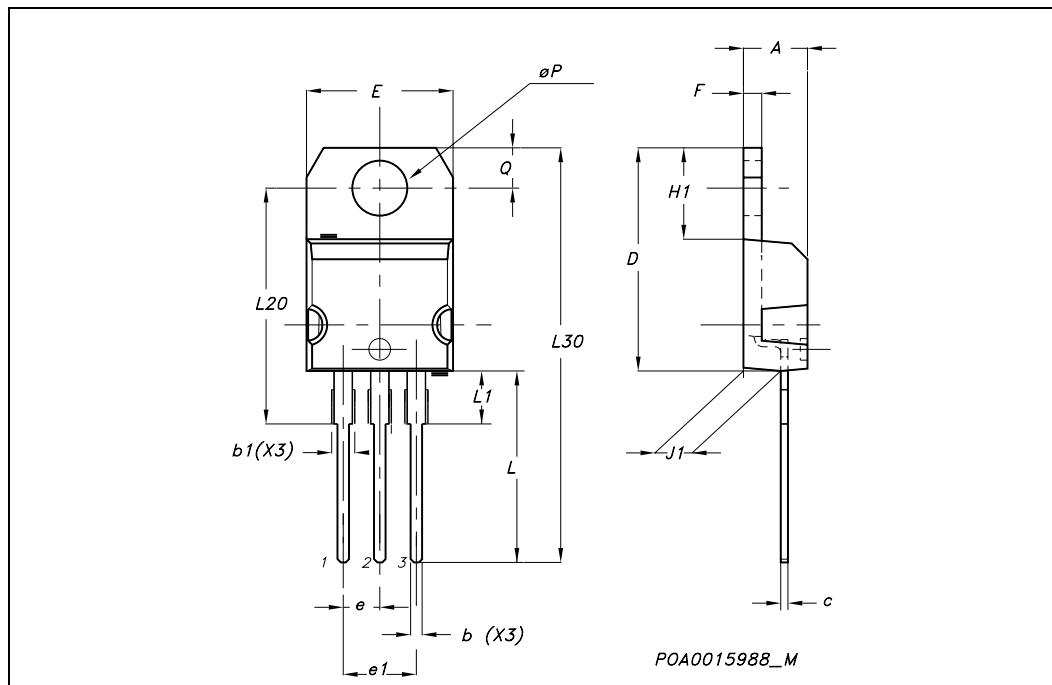
TO-262 (I<sup>2</sup>PAK) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



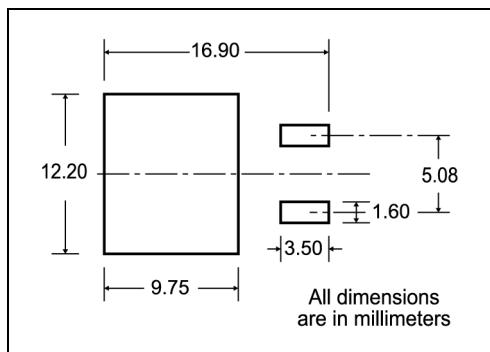
## TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



## 5 Packaging mechanical data

### D<sup>2</sup>PAK FOOTPRINT



### TAPE AND REEL SHIPMENT

REEL MECHANICAL DATA				
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A			330	12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197
BASE QTY		BULK QTY		
1000		1000		

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

\* on sales type

## 6 Revision history

**Table 6. Revision history**

Date	Revision	Changes
21-Jun-2006	1	First document
19-Jun-2006	2	New template, no content change

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